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Advanced Calculations for Defects in Materials

Electronic Structure Methods



WILEY-VCH Verlag GmbH & Co. KGaA

The Editors

Dr. Audrius Alkauskas EPFL 58. IPMC LSME

MX 136 Batiment MXC 12 1015 Lausanne

Schweiz

Prof. Dr. Peter Deák

Uni Bremen - Computational Materials Science Otto-Hahn-Allee 1 28359 Bremen

Prof. Dr. Jörg Neugebauer Fritz-Haber-Institut

Max-Planck-Inst. f. Eisenfor. Max-Planck-Str. 1

40237 Düsseldorf

Prof. Dr. Alfredo Pasquarello

EPFL-SB-ITP-CSEA Station 3/ PH H2 467 1015 Lausanne Schweiz

Prof. Dr. C. G. Van de Walle

Materials Department University of California Santa Barbara, CA 93106-5050 USA All books published by Wiley-VCH are carefully produced. Nevertheless, authors, editors, and publisher do not warrant the information contained in these books, including this book, to be free of errors. Readers are advised to keep in mind that statements, data, illustrations, procedural details or other items may inadvertently be inaccurate.

Library of Congress Card No.: applied for

British Library Cataloguing-in-Publication Data

A catalogue record for this book is available from the British Library.

Bibliographic information published by the Deutsche Nationalbibliothek The Deutsche Nationalbibliothek lists this

The Deutsche Nationalbibliothek lists this publication in the Deutsche Nationalbibliografie; detailed bibliographic data are available on the Internet at http://dnb.d-nb.de.

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Composition Thomson Digital, Noida, India Printing and Binding strauss GmbH, Mörlenbach Cover Design Adam-Design, Weinheim

Printed in the Federal Republic of Germany Printed on acid-free paper

ISBN: 978-3-527-41024-8

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List of Contributors

Audrius Alkauskas

Ecole Polytechnique Fédérale de Lausanne (EPFL) Institute of Theoretical Physics 1015 Lausanne Switzerland

and

Institut Romand de Recherche Numérique en Physique des Matériaux (IRRMA) 1015 Lausanne Switzerland

Bálint Aradi

Universität Bremen Bremen Center for Computational Materials Science Am Fallturm 1 28359 Bremen Germany

Stefano Baroni

CNR-IOM DEMOCRITOS Theory@Elettra Group s.s. 14 km 163.5 in Area Science Park 34149 Basovizza (Trieste) Italy

and

SISSA – Scuola Internazionale Superiore di Studi Avanzati via Bonomea 265 34126 Trieste Italy

Adisak Boonchun

Case Western Reserve University Department of Physics 10900 Euclid Avenue Cleveland, OH 444106-7079 USA

Patrick R. Briddon

Newcastle University School of Electrical, Electronic and Computer Engineering Newcastle NE1 7RU UK

Peter Broqvist

Ecole Polytechnique Fédérale de Lausanne (EPFL) Institute of Theoretical Physics 1015 Lausanne Switzerland

and

Institut Romand de Recherche Numérique en Physique des Matériaux (IRRMA) 1015 Lausanne Switzerland

Fabien Bruneval

European Theoretical Spectroscopy Facility (ETSF)

and

CEA, DEN, Service de Recherches de Métallurgie Physique 91191 Gif-sur-Yvette France

G. Bussi

Universita di Modena e Reggio Emilia CNR-NANO, S3 and Dipartimento di Fisica via Campi 213/A 41100 Modena Italy

and

CNR-IOM Democritos and SISSA via Bonomea 265 34136 Trieste Italy

Marilia I. Caldas

Universidade de São Paulo Instituto de Física 05508-900 São Paulo, SP Brazil

S. J. Clark

Durham University Physics Department Durham UK

Peter Deák

Universität Bremen Bremen Center for Computational Materials Science Am Fallturm 1 28359 Bremen Germany

Thomas Frauenheim

Universität Bremen Bremen Center for Computational Materials Science Aon Fallturon 28359 Bremen Germany

Christoph Freysoldt

Max-Planck-Institut für Eisenforschung GmbH Max-Planck-Str. 1 40237 Düsseldorf Germany

Adam Gali

Hungarian Academy of Sciences Research Institute for Solid State Physics and Optics POB 49 1525 Budapest Hungary

and

Budapest University of Technology and Economics Department of Atomic Physics Budafoki út 8 1111 Budapest Hungary

Uwe Gerstmann

Universität Paderborn Lehrstuhl für Theoretische Physik Warburger Str. 100 33098 Paderborn Germany

and

Université Pierre et Marie Curie Institut de Minéralogie et de Physique des Milieux Condensés Campus Boucicaut 140 rue de Lourmel 75015 Paris France

Luigi Giacomazzi

CNR-IOM DEMOCRITOS Theory@Elettra Group s.s. 14 km 163.5 in Area Science Park 34149 Basovizza (Trieste) Italy

and

SISSA - Scuola Internazionale Superiore di Studi Avanzati via Bonomea 265 34126 Trieste Italy

Matteo Giantomassi

European Theoretical Spectroscopy Facility (ETSF)

and

Université catholique de Louvain Institute of Condensed Matter and Nanosciences 1 Place Croix du Sud. 1 bte 3 1348 Louvain-la-Neuve Belgium

Blazej Grabowski

Max-Planck-Institut für Eisenforschung GmbH Max-Planck-Str. 1 40237 Düsseldorf Germany

Myrta Grüning

European Theoretical Spectroscopy Facility (ETSF)

and

University of Coimbra Centre for Computational Physics and Physics Department Rua Larga 3004-516 Coimbra Portugal

Thomas M. Henderson

Rice University Departments of Chemistry and Department of Physics and Astronomy Houston, TX 77005 USA

Richard G. Hennig

Cornell University Department of Materials Science and Engineering 126 Bard Hall Ithaca, NY 14853-1501 USA

Tilmann Hickel

Max-Planck-Institut für Eisenforschung GmbH Max-Planck-Str. 1 40237 Düsseldorf Germany

Anderson Janotti

University of California Materials Department Santa Barbara, CA 93106-5050 USA

Walter R. L. Lambrecht

Case Western Reserve University Department of Physics 10900 Euclid Avenue Cleveland, OH 444106-7079 **USA**

Stephan Lany

National Renewable Energy Laboratory 1617 Cole Blvd Golden, CO 80401 **USA**

L. Martin-Samos

Universita di Modena e Reggio Emilia CNR-NANO, S3 and Dipartimento di Fisica via Campi 213/A 41100 Modena Italy

and

CNR-IOM Democritos and SISSA via Bonomea 265 34136 Trieste Italy

Nicola Marzari

Massachusetts Institute of Technology Department of Materials Science and Engineering 77 Massachusetts Avenue Cambridge, MA 02139 USA

E. Molinari

Universita di Modena e Reggio Emilia CNR-NANO, S3 and Dipartimento di Fisica via Campi 213/A 41100 Modena Italy

Jörg Neugebauer

Max-Planck-Institut für Eisenforschung GmbH Max-Planck-Str. 1 40237 Düsseldorf Germany

Joachim Paier

Rice University Departments of Chemistry and Department of Physics and Astronomy Houston, TX 77005 **USA**

Present affiliation: Humboldt-Universität Zu Berlin Institut für Chemie Unter den Linden 6 10099 Berlin Germany

William D. Parker

The Ohio State University Department of Physics 191 W. Woodruff Ave. Columbus, OH 43210 USA

Alfredo Pasquarello

Ecole Polytechnique Fédérale de Lausanne (EPFL) Institute of Theoretical Physics 1015 Lausanne Switzerland

and

Institut Romand de Recherche Numérique en Physique des Matériaux (IRRMA) 1015 Lausanne Switzerland

Xiaofeng Qian

Massachusetts Institute of Technology Department of Materials Science and Engineering 77 Massachusetts Avenue Cambridge, MA 02139 **USA**

Mark J. Rayson

Max-Planck-Institut für Eisenforschung GmbH Max-Planck-Str. 1 40237 Düsseldorf Germany

and

Luleå University of Technology Department of Mathematics 97187 Luleå Sweden

Gian-Marco Rignanese

European Theoretical Spectroscopy Facility (ETSF)

and

Université catholique de Louvain Institute of Condensed Matter and Nanosciences 1 Place Croix du Sud. 1 bte 3 1348 Louvain-la-Neuve Belgium

Patrick Rinke

European Theoretical Spectroscopy Facility (ETSF)

and

University of California Department of Materials Santa Barbara, CA 93106-5050 USA

John Robertson

Cambridge University **Engineering Department** Cambridge CB2 1PZ UK

A. Ruini

Universita di Modena e Reggio Emilia CNR-NANO, S3 and Dipartimento di Fisica via Campi 213/A 41100 Modena Italy

Gustavo E. Scuseria

Rice University Departments of Chemistry and Physics and Astronomy Houston, TX 77005 USA

Riad Shaltaf

European Theoretical Spectroscopy Facility (ETSF)

and

University of Jordan Department of Physics Amman 11942 Iordan

Martin Stankovski

European Theoretical Spectroscopy Facility (ETSF)

and

Université catholique de Louvain Institute of Condensed Matter and Nanosciences 1 Place Croix du Sud, 1 bte 3 1348 Louvain-la-Neuve Belgium

Geoffoey Stenuit

CNR-IOM DEMOCRITOS Theory@Elettra Group s.s. 14 km 163.5 in Area Science Park 34149 Basovizza (Trieste) Italy

Paolo Umari

CNR-IOM DEMOCRITOS Theory@Elettra Group s.s. 14 km 163.5 in Area Science Park 34149 Basovizza (Trieste) Italy

Chris G. Van de Walle

University of California Materials Department Santa Barbara, CA 93106-5050 USA

Su-Huai Wei

National Renewable Energy Laboratory 1617 Cole Blvd Golden, CO 80401 USA

John W. Wilkins

The Ohio State University Department of Physics 191 W. Woodruff Ave. Columbus, OH 43210 USA

Yanfa Yan

National Renewable Energy Laboratory 1617 Cole Blvd Golden, CO 80401 USA